

Zero Recovery Silicon Carbide Schottky Diode

PRODUCT APPLICATIONS

- Anti-Parallel Diode

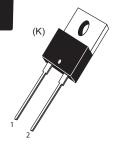
 Switchmode Power Supply
 Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Time (t_{rr})
- Popular TO-220 Package
- · Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates snubber





1 - Cathode 2 - Anode Back of Case - Cathode

MAXIMUM RATINGS

 $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage				
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		650	Volts	
V_{RWM}	Maximum Working Peak Reverse Voltage]			
	Maximum D.C. Forward Current	T _c = 25°C	32		
I _F		T _C = 90°C	20		
I _{FRM}	Repetitive Peak Forward Surge Current (T _C = 25°C, t _p = 10ms, Half Sine Wave)		75	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _c = 25°C, t _p = 10ms, Half Sine)		165		
Ртот	Power Dissipation	T _C = 25°C	114	W	
		T _C = 110°C	36		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to 150	- °C	
T _L	Lead Temperature for 10 Seconds		300		

STATIC ELECTRICAL CHARACTERISTICS

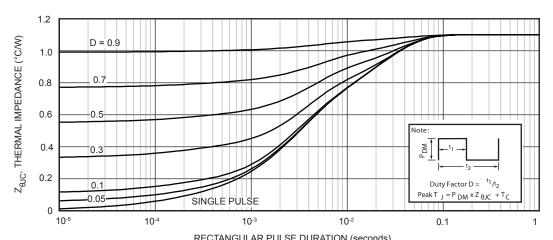
Symbol	Characteristic / Test Conditions		Min	Тур	Max	Unit
$V_{_{\rm F}}$	Forward Voltage	I _F = 20A T _J = 25°C		1.5	1.8	Volts
		I _F = 20A, T _J = 150°C		1.9		
I _{RM}	Maximum Reverse Leakage Current	V _R = 650V T _J = 25°C		20	400	μΑ
		V _R = 650V, T _J = 150°C		250		
Q _c	Total Capactive Charge V_R = 325V, I_F = 20A, di/dt = -500A/ μ s, T_J = 25°C			100		nC
C _T	Junction Capacitance $V_R = 0.1V$, $T_J = 25$ °C, $f = 1$ MHz			680		pF
	Junction Capacitance V _R = 200V, T _J = 25°C, f = 1MHz			89		
	Junction Capacitance $V_R = 400V$, $T_J = 25^{\circ}C$, $f = 1MHz$			73		

THERMAL AND MECHANICAL CHARACTERISTICS

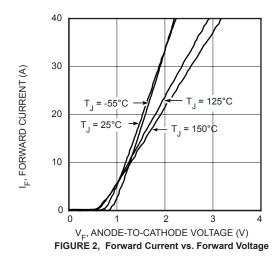
Symbol	Characteristic / Test Conditions	Min	Тур	Max	Unit
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.1	°C/W
W _T	Package Weight		0.07		oz
			1.9		g
Torque	Maximum Mounting Torque			6.4	lb∙in
				0.7	N·m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES



RECTANGULAR PULSE DURATION (seconds)
FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



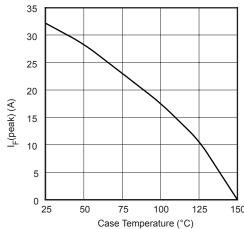


FIGURE 3, Maximum Forward Current vs. Case Temperature

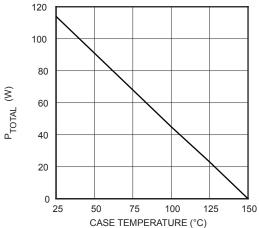


Figure 4. Maximum Power Dissipation vs. Case Temperature

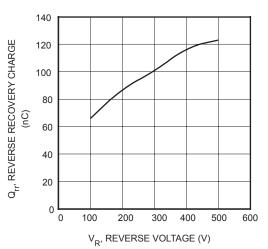


Figure 6. Reverse Recovery Charge vs. V_R

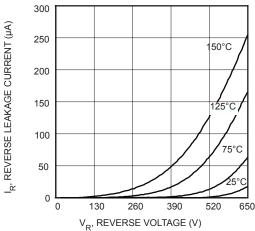
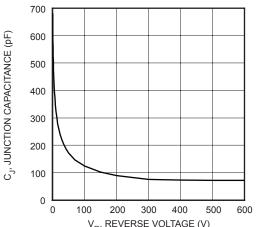


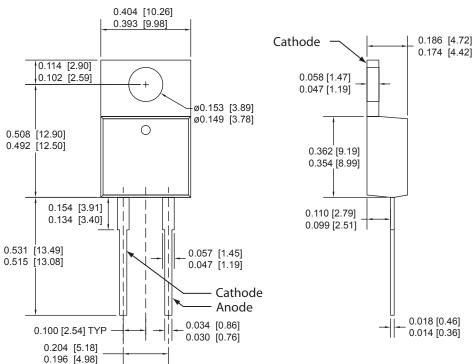
Figure 5. Reverse Leakage Currents vs. Reverse Voltage



 ${\rm V_{R}, REVERSE\ VOLTAGE\ (V)}$ Figure 7. Junction Capacitance vs. Reverse Voltage

TO-220 (K) Package Outline

e3 100% Sn



Dimensions in Millimeters and (Inches)

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